

wherein said gate insulating film includes a layer of a silicon nitride oxide film containing boron.

2. (Amended) A semiconductor device according to claim 1, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

3. (Amended) A semiconductor device according to claim 1, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

4. (Amended) A semiconductor device according to claim 1, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

cont
A1 5. (Amended) A semiconductor device according to claim 4, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

6. (Amended) A semiconductor device according to claim 4, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.

7. (Amended) A semiconductor device comprising:
a source region, a drain region, and a channel formation region formed between said source region and said drain

region, the respective regions being in contact with an insulating surface;

a gate insulating film comprising at least single layer on said channel formation region; and

a gate electrode to be in contact with said gate insulating film;

wherein said gate insulting film includes a layer of a silicon nitride oxide film containing boron.

8. (Amended) A semiconductor device according to claim 7, wherein a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

9. (Amended) A semiconductor device according to claim 7, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

cont, A 1 10. (Amended) A semiconductor device according to claim 7, wherein said semiconductor is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

11. (Amended) A semiconductor device according to claim 10, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, and EC display device, and an image sensor.

12. (Amended) A semiconductor device according to claim 10 wherein said electronic equipment is one selected from group

cont. consisting of a video camera, a digital camera, a projector, a
A1 goggle display, a car navigation system, a personal computer, and
a portable information terminal.

14. (Amended) A semiconductor device according to claim
13, wherein a composition ration of boron in said silicon nitride
oxide film is 0.1 to 50 atoms%.

15. (Amended) A semiconductor device according to claim
13, wherein a composition ratio of oxygen in said silicon nitride
oxide film is 1 to 30 atoms%.

16. (Amended) A semiconductor device according to claim
13, wherein said semiconductor device is incorporated into a
device selected from the group consisting of an electro-optical
device and an electronic equipment.

A2 17. (Amended) A semiconductor device according to claim 16,
wherein said electro-optical device is one selected from group
consisting of a liquid crystal display device, an EL display
device, an EC display device, and an image sensor.

18. (Amended) A semiconductor device according to claim 16,
wherein said electronic equipment is one selected from the group
consisting of a video camera, a digital camera, a projector, a
goggle display, a car navigation system, a personal computer and
a portable information terminal.

20. (Amended) A semiconductor device according to claim 19, where a composition ratio of boron in said silicon nitride oxide film is 0.1 to 50 atoms%.

21. (Amended) A semiconductor device according to claim 19, wherein a composition ratio of oxygen in said silicon nitride oxide film is 1 to 30 atoms%.

22. (Amended) A semiconductor device according to claim 19, wherein said semiconductor device is incorporated into a device selected from the group consisting of an electro-optical device and an electronic equipment.

A3 23. (Amended) A semiconductor device according to claim 22, wherein said electro-optical device is one selected from the group consisting of a liquid crystal display device, an EL display device, an EC display device, and an image sensor.

24. (Amended) A semiconductor device according to claim 22, wherein said electronic equipment is one selected from the group consisting of a video camera, a digital camera, a projector, a goggle display, a car navigation system, a personal computer, and a portable information terminal.